Unit in mm

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE

2 S A 1 8 1 1

LOW FREQUENCY AMPLIFIER APPLICATIONS. DRIVER STAGE AMPLIFIER APPLICATIONS. SWITCHING APPLICATIONS.

- Excellent hFE Linearity
 - : $h_{FE(2)} = 35 \text{ (Min.)}, (V_{CE} = -2V, I_{C} = -300 \text{mA})$
- Complementary to 2SC4707

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	-35	V
Collector-Emitter Voltage	v_{CEO}	-30	V
Emitter-Base Voltage	v_{EBO}	-5	V
Collector Current	$I_{\mathbf{C}}$	-500	mA
Base Current	I_{B}	-100	mA
Collector Power Dissipation	PC	800	mW
Junction Temperature	T_j	150	$^{\circ}\mathrm{C}$
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	°C

5.1 MAX 1.0 MAX 0.8 MAX 0.5 MIN 0.6 MAX **EMITTER** COLLECTOR BASE **JEDEC** TO-92MOD **EIAJ** TOSHIBA 2-5J1A

Weight: 0.36g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -35V, I_{E} = 0$		_	-0.1	μ A
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB} = -5V, I_{C} = 0$		_	-0.1	μ A
DC Current Gain	$_{ m h_{FE}(1)}$	$V_{CE} = -2V, I_{C} = -100 \text{mA}$	100	_	300	
	$h_{ ext{FE}(2)}$	$V_{CE} = -2V, I_{C} = -300 \text{mA}$	35	_	_	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	$I_{C} = -300 \text{mA}, I_{B} = -30 \text{mA}$	_	-0.2	-0.5	V
Base-Emitter Voltage	$ m V_{BE}$	$V_{CE} = -2V, I_{C} = -100 \text{mA}$	_	-0.8	-1.0	V
Transition Frequency	$ m f_{T}$	$V_{CE} = -6V, I_{C} = -20mA$	_	200	_	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -6V, I_{E} = 0, f = 1MHz$	_	9	_	рF

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